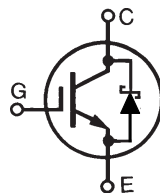


GenX3™ 600V IGBT w/ SiC Anti-Parallel Diode

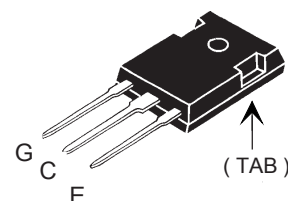
IXGH48N60B3C1



V_{CES}	=	600V
I_{C110}	=	48A
$V_{CE(sat)}$	≤	1.8V
$t_{fi(typ)}$	=	116ns

Medium Speed Low Vsat PT
IGBT 5 - 40 kHz Switching

TO-247



G = Gate C = Collector
E = Emitter TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1\text{M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Limited by Leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	48	A
I_{F110}	$T_C = 110^\circ\text{C}$	20	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	280	A
SSOA (RBSOA)	$V_{GE} = 15\text{V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 120$ @ $\leq V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- Anti-Parallel Schottky Diode
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0\text{V}$	600		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$ $T_J = 125^\circ\text{C}$			50 μA 1.75 mA
I_{GES}	$V_{CE} = 0\text{V}$, $V_{GE} = \pm 20\text{V}$			±100 nA
$V_{CE(sat)}$	$I_C = 32\text{A}$, $V_{GE} = 15\text{V}$, Note 1			1.8 V

Symbol Test Conditions

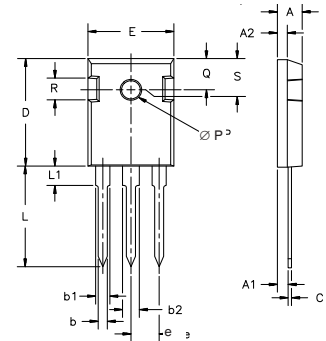
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 30\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	28	46	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3980	pF
C_{oes}			190	pF
C_{res}			45	pF
Q_g	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		115	nC
Q_{ge}			21	nC
Q_{gc}			40	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		22	ns
t_{ri}			26	ns
E_{on}			0.45	mJ
$t_{d(off)}$			130	ns
t_{fi}			116	ns
E_{off}			0.66	mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		22	ns
t_{ri}			26	ns
E_{on}			0.50	mJ
$t_{d(off)}$			190	ns
t_{fi}			157	ns
E_{off}			1.30	mJ
R_{thJC}			0.42	$^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

TO-247 (IXGH) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode (SiC)

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$	1.65	2.10	V
	$T_J = 125^\circ\text{C}$	1.80		V
R_{thJC}			0.90	$^\circ\text{C/W}$

Notes

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

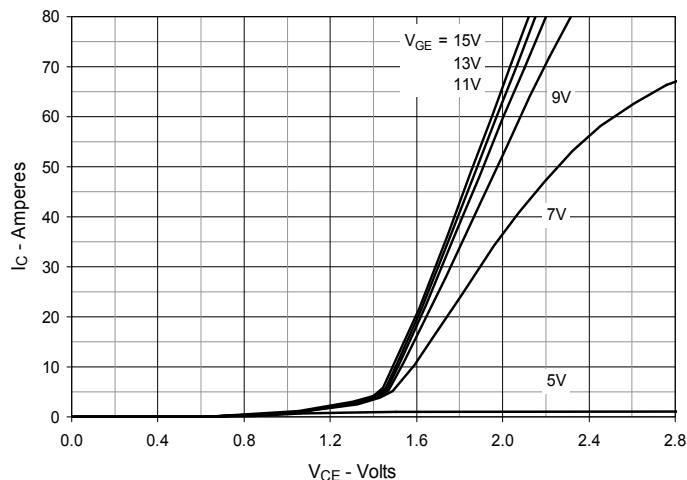


Fig. 2. Extended Output Characteristics
@ 25°C

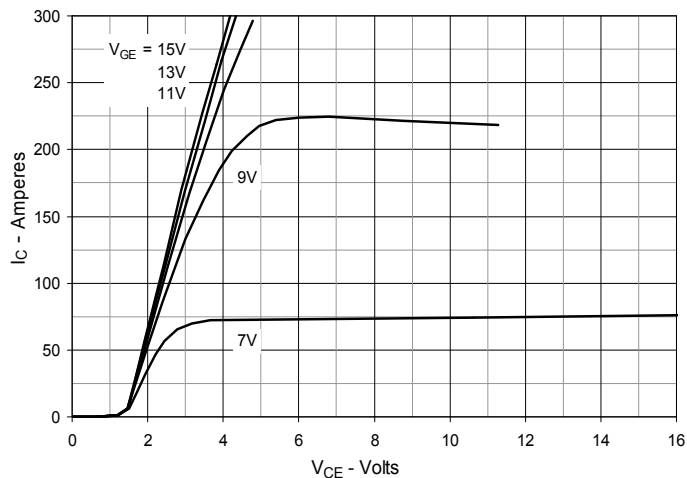


Fig. 3. Output Characteristics
@ 125°C

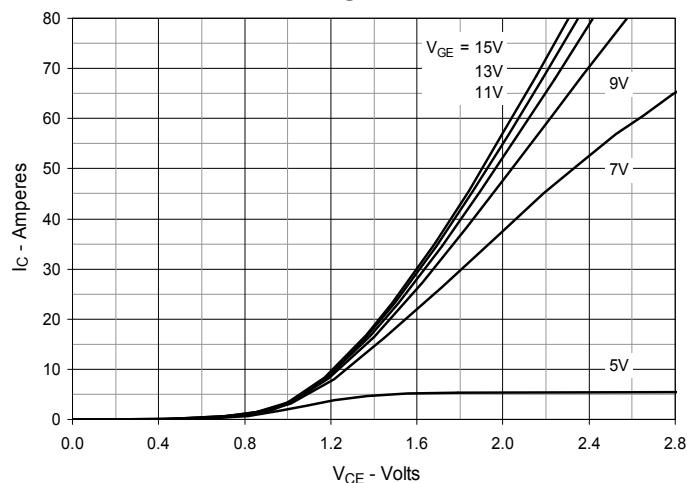


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

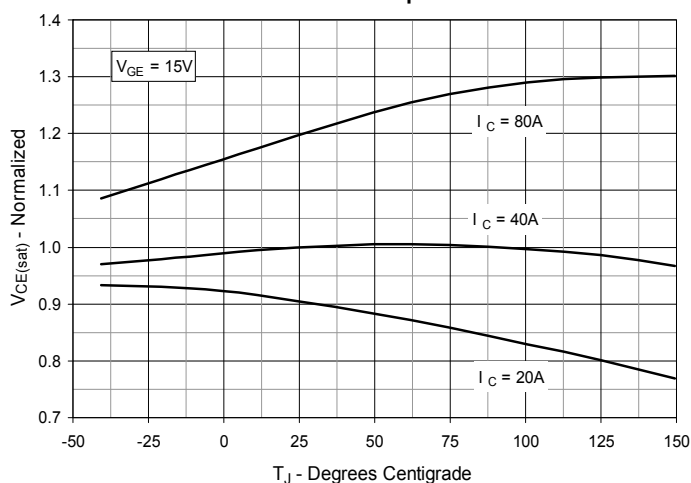


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

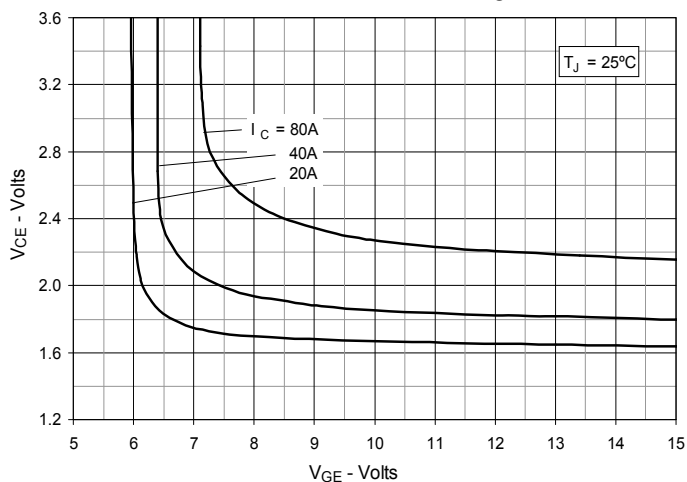


Fig. 6. Input Admittance

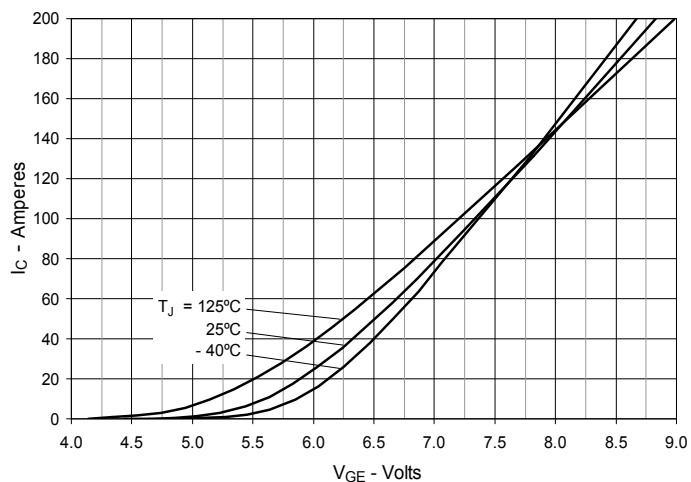


Fig. 7. Transconductance

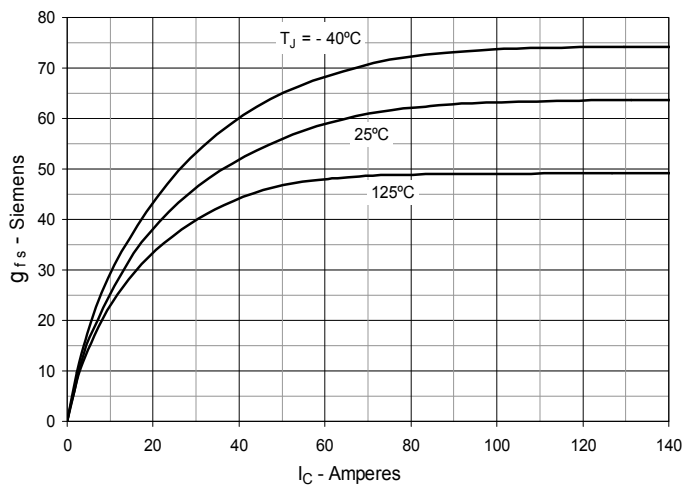


Fig. 8. Gate Charge

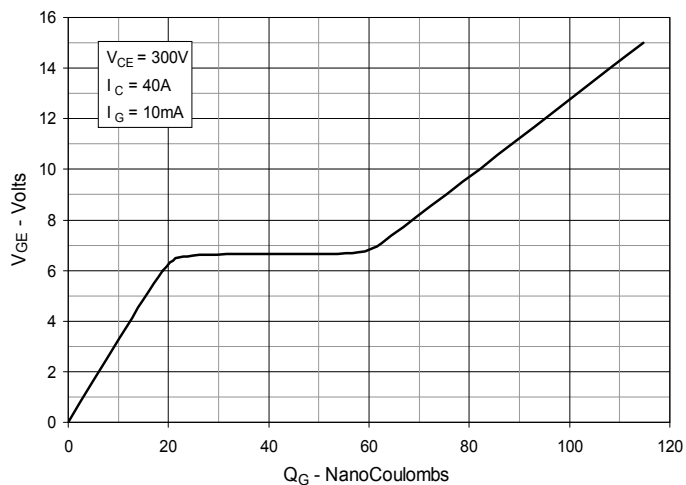


Fig. 9. Capacitance

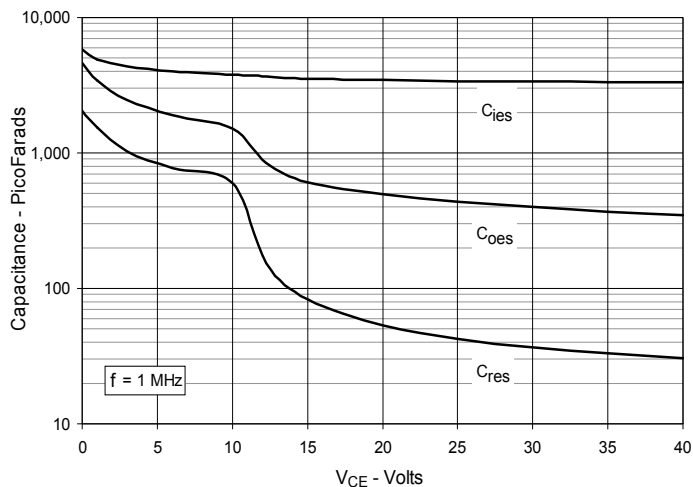


Fig. 10. Reverse-Bias Safe Operating Area

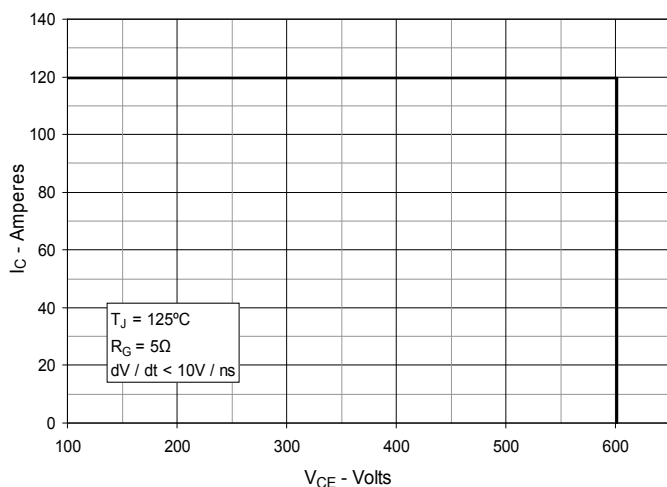
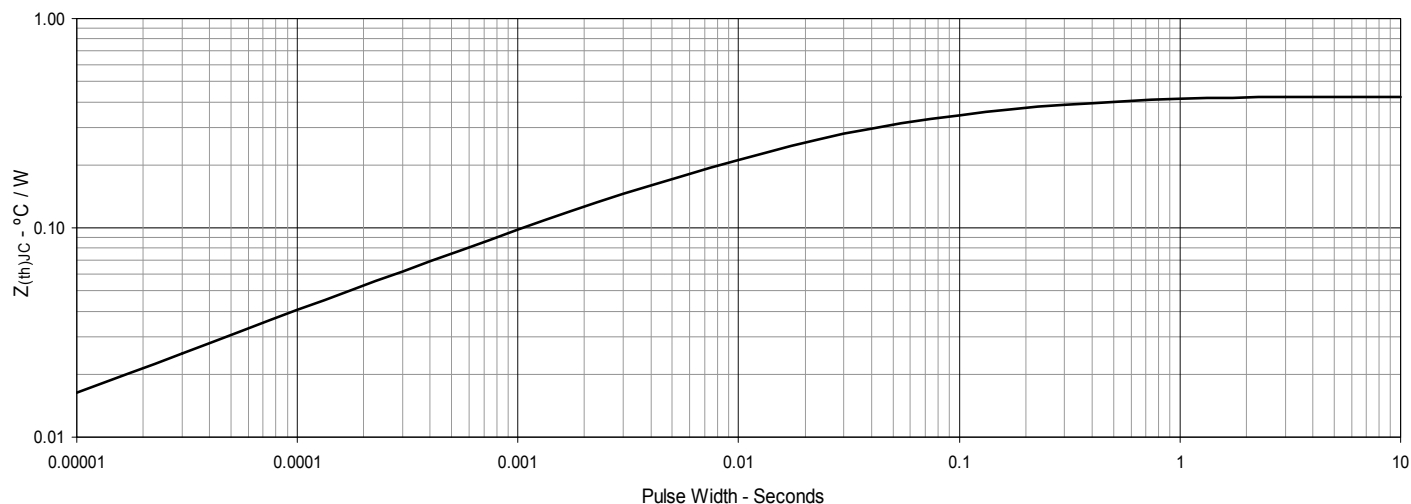
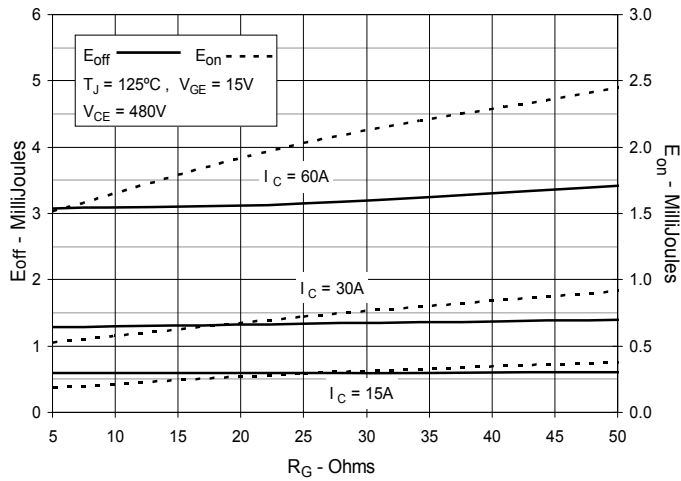


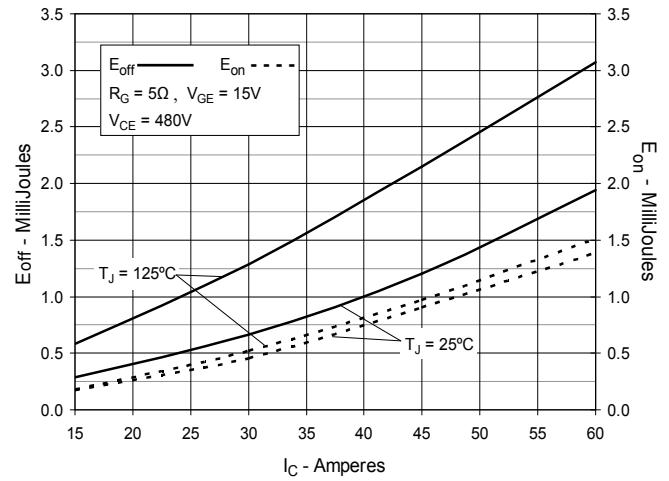
Fig. 11. Maximum Transient Thermal Impedance for IGBT



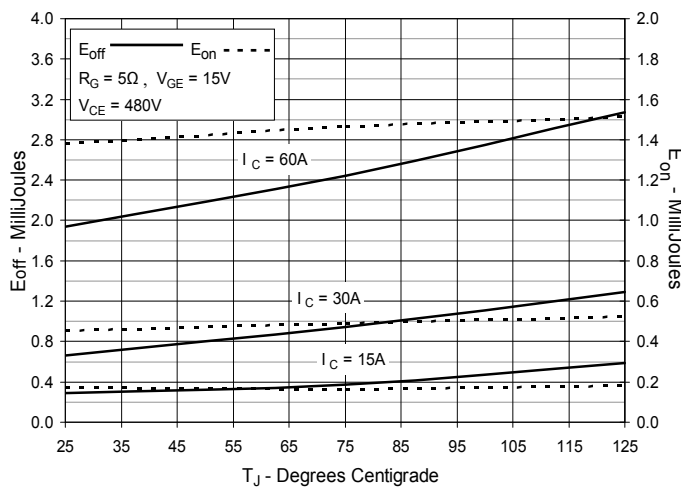
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



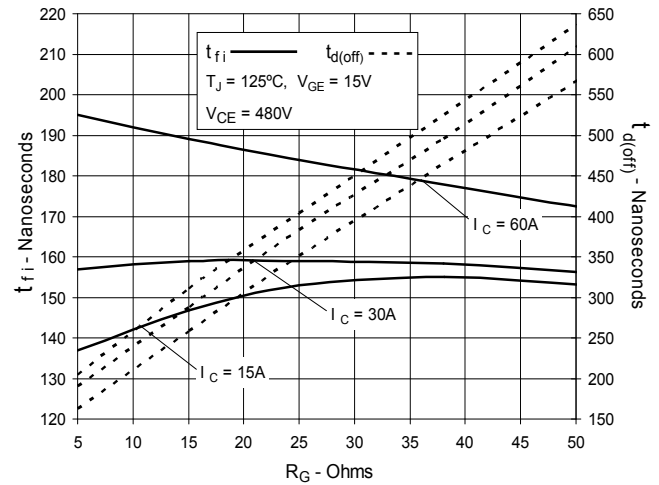
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



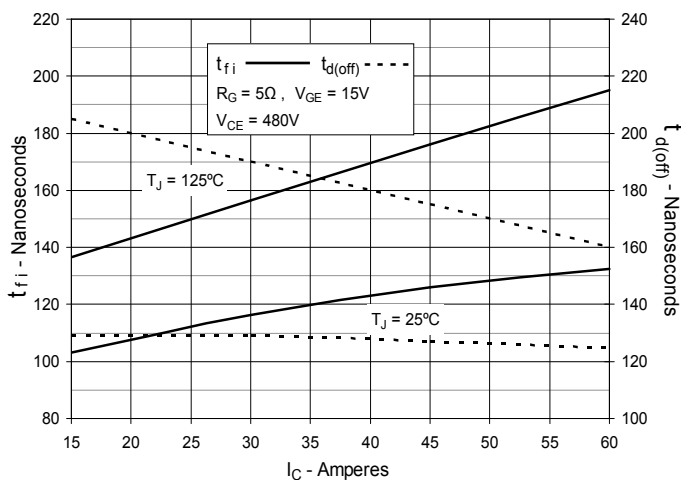
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



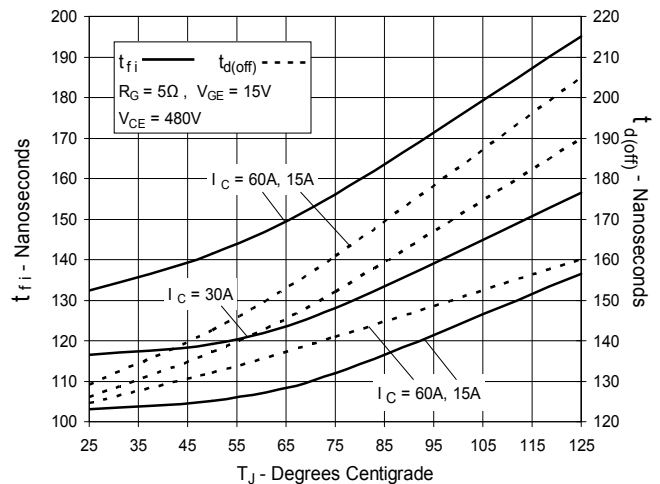
**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



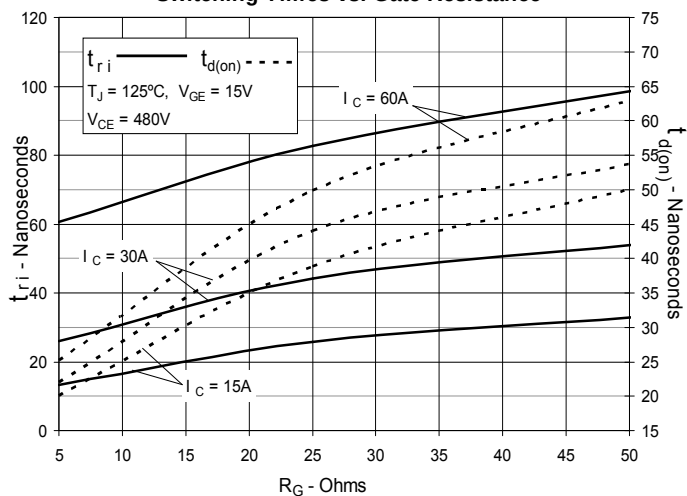
**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



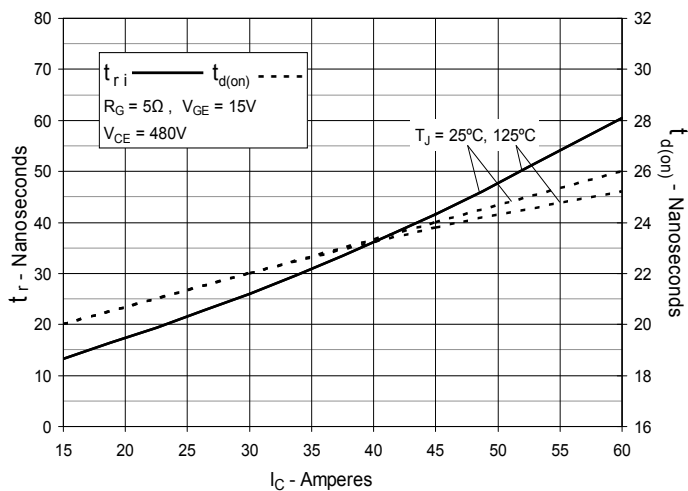
**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance**



**Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current**



**Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature**

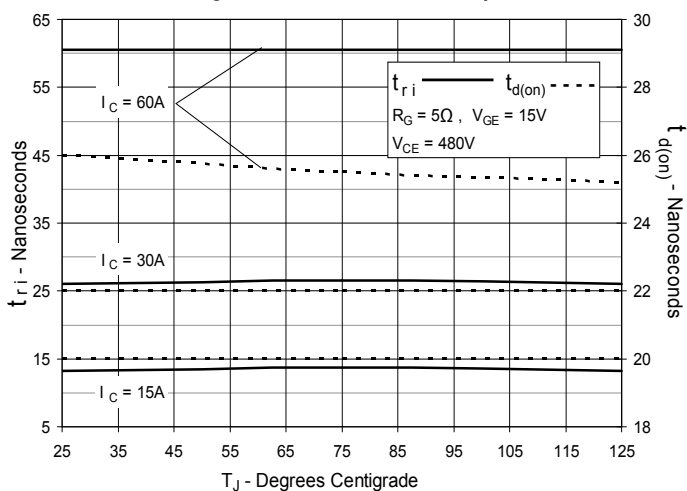


Fig. 21. Forward Current vs. Forward Voltage

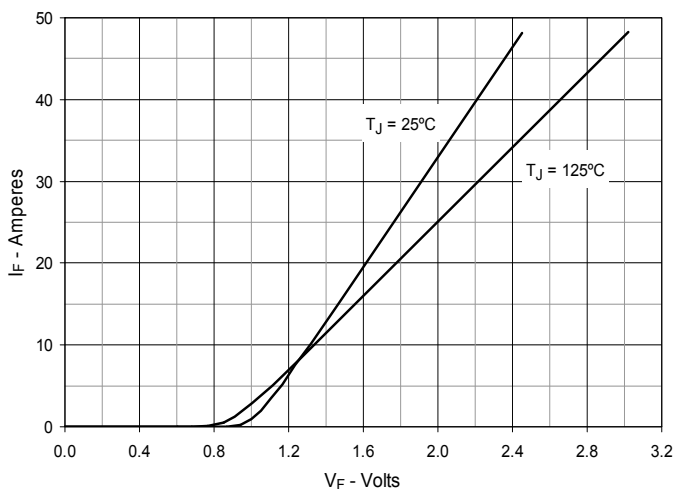


Fig. 22. Maximum Transient Thermal Impedance for Diodes

